Chaker Fares

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619 12 21 54 h-index g-index citations papers 65 825 4.29 2.7 L-index avg, IF ext. citations ext. papers

#	Paper	IF	Citations
54	Radiation damage effects in Ga2O3 materials and devices. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 10)-2 / 1.1	90
53	Unipolar Electron Transport Polymers: A Thiazole Based All-Electron Acceptor Approach. <i>Chemistry of Materials</i> , 2016 , 28, 6045-6049	9.6	64
52	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated EGa2O3. <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
51	Temperature-Dependent Electrical Characteristics of EGa2O3Diodes with W Schottky Contacts up to 500 Cc. ECS Journal of Solid State Science and Technology, 2019 , 8, Q3007-Q3012	2	28
50	Vertical geometry 33.2 A, 4.8 MW cm2 Ga2O3 field-plated Schottky rectifier arrays. <i>Applied Physics Letters</i> , 2019 , 114, 232106	3.4	26
49	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted EGa2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3133-Q3139	2	20
48	Valence- and Conduction-Band Offsets for Atomic-Layer-Deposited Al2O3 on (010) (Al0.14Ga0.86)2O3. <i>Journal of Electronic Materials</i> , 2019 , 48, 1568-1573	1.9	19
47	The role of annealing ambient on diffusion of implanted Si in EGa2O3. AIP Advances, 2019, 9, 085111	1.5	18
46	Reverse Breakdown in Large Area, Field-Plated, Vertical EGa2O3Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3159-Q3164	2	16
45	Effects of fluorine incorporation into EGa2O3. Journal of Applied Physics, 2018, 123, 165706	2.5	16
44	Band alignment of atomic layer deposited SiO2 on (010) (Al0.14Ga0.86)2O3. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 061207	1.3	15
43	Eighteen mega-electron-volt alpha-particle damage in homoepitaxial EGa2O3 Schottky rectifiers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 031205	1.3	13
42	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, EGa2O3Vertical Geometry Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3028-Q3033	2	12
41	Valence band offsets for CuI on (-201) bulk Ga2O3 and epitaxial (010) (Al0.14Ga0.86)2O3. <i>Applied Physics Letters</i> , 2018 , 113, 182101	3.4	12
40	Forward bias degradation and thermal simulations of vertical geometry EGa2O3 Schottky rectifiers. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2019 , 37, 061205	1.3	11
39	Device processing and junction formation needs for ultra-high power Ga2O3 electronics. <i>MRS Communications</i> , 2019 , 9, 77-87	2.7	11
38	Anti-Bacterial Properties and Biocompatibility of Novel SiC Coating for Dental Ceramic. <i>Journal of Functional Biomaterials</i> , 2020 , 11,	4.8	11

(2019-2018)

37	Effect of proton irradiation energy on SiNx/AlGaN/GaN metal-insulator semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2018 , 36, 052202	1.3	11
36	Effect of probe geometry during measurement of >100 A Ga2O3 vertical rectifiers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 013406	2.9	11
35	Effect of thermal annealing for W/EGa2O3 Schottky diodes up to 600 LC. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2019 , 37, 061201	1.3	10
34	60Co Gamma Ray Damage in Homoepitaxial EGa2O3Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3041-Q3045	2	10
33	Demonstration of a SiC Protective Coating for Titanium Implants. <i>Materials</i> , 2020 , 13,	3.5	10
32	Valence and Conduction Band Offsets for InN and III-Nitride Ternary Alloys on (201) Bulk EGa2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3154-Q3158	2	9
31	Valence band offsets for ALD SiO2 and Al2O3 on (InxGa1 \mathbb{N})2O3 for x = 0.25 \mathbb{N} .74. <i>APL Materials</i> , 2019 , 7, 071115	5.7	9
30	Effect of Deposition Method on Valence Band Offsets of SiO2 and Al2O3 on (Al0.14Ga0.86)2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3001-Q3006	2	9
29	Band Alignment of Atomic Layer Deposited SiO2 and Al2O3 on (AlxGa1-x)2O3 for $x = 0.2-0.65$. ECS Journal of Solid State Science and Technology, 2019 , 8, P351-P356	2	8
28	Band Offsets for Atomic Layer Deposited HfSiO4 on (Al0.14Ga0.86)2O3. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P519-P523	2	8
27	Demonstration of SiO/SiC based protective coating for dental ceramic prostheses. <i>Journal of the American Ceramic Society</i> , 2019 , 102, 6591-6599	3.8	7
26	Novel Coatings to Minimize Bacterial Adhesion and Promote Osteoblast Activity for Titanium Implants. <i>Journal of Functional Biomaterials</i> , 2020 , 11,	4.8	7
25	Novel Coating to Minimize Corrosion of Glass-Ceramics for Dental Applications. <i>Materials</i> , 2020 , 13,	3.5	7
24	Fast SARS-CoV-2 virus detection using disposable cartridge strips and a semiconductor-based biosensor platform. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2021 , 39, 033202	1.3	6
23	Valence and conduction band offsets for sputtered AZO and ITO on (010) (Al0.14Ga0.86)2O3. <i>Semiconductor Science and Technology</i> , 2019 , 34, 025006	1.8	6
22	OH-Si complex in hydrogenated n-type EGa2O3:Si. <i>Applied Physics Letters</i> , 2021 , 119, 062109	3.4	6
21	Temperature dependent performance of ITO Schottky contacts on EGa2O3. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 053405	2.9	6
20	Band Offsets of Insulating & Semiconducting Oxides on (AlxGa1-x)O3. <i>ECS Transactions</i> , 2019 , 92, 79-8	8 1	5

19	Asymmetrical Contact Geometry to Reduce Forward-Bias Degradation in EGa2O3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 035007	2	5
18	Rapid Electrochemical Detection for SARS-CoV-2 and Cardiac Troponin I Using Low-Cost, Disposable and Modular Biosensor System 2020 ,		4
17	Vertical EGa2O3 Schottky rectifiers with 750 V reverse breakdown voltage at 600 K. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 305103	3	4
16	Effect of Annealing on the Band Alignment of ALD SiO2 on (AlxGa1-x)2O3 for $x = 0.2 - 0.65$. ECS Journal of Solid State Science and Technology, 2019 , 8, P751-P756	2	4
15	Novel Coatings to Minimize Corrosion of Titanium in Oral Biofilm. <i>Materials</i> , 2021 , 14,	3.5	4
14	Hydroxyapatite Formation on Coated Titanium Implants Submerged in Simulated Body Fluid. <i>Materials</i> , 2020 , 13,	3.5	3
13	Changes in band alignment during annealing at 600 $\mbox{\em C}$ of ALD Al2O3 on (InxGa1 $\mbox{\em B}$)2O3 for x = 0.25 $\mbox{\em D}$.74. <i>Journal of Applied Physics</i> , 2020 , 127, 105701	2.5	3
12	Qualitative Analysis of Remineralization Capabilities of Bioactive Glass (NovaMin) and Fluoride on Hydroxyapatite (HA) Discs: An In Vitro Study. <i>Materials</i> , 2021 , 14,	3.5	3
11	Nanostructured Surfaces to Promote Osteoblast Proliferation and Minimize Bacterial Adhesion on Titanium. <i>Materials</i> , 2021 , 14,	3.5	3
10	Nitrogen ion-implanted resistive regions for edge termination of vertical Ga2O3 rectifiers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 063405	2.9	3
9	Annealing and N Plasma Treatment to Minimize Corrosion of SiC-Coated Glass-Ceramics. <i>Materials</i> , 2020 , 13,	3.5	2
8	Deep traps and persistent photocapacitance in E(Al0.14 Ga0.86)2O3/Ga2O3 heterojunctions. <i>Journal of Applied Physics</i> , 2019 , 125, 095702	2.5	1
7	Titanium Corrosion in Peri-Implantitis. <i>Materials</i> , 2020 , 13,	3.5	1
6	Band offset determination for amorphous Al2O3 deposited on bulk AlN and atomic-layer epitaxial AlN on sapphire. <i>Applied Physics Letters</i> , 2020 , 117, 182103	3.4	1
5	Digital biosensor for human cerebrospinal fluid detection with single-use sensing strips. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2022 , 40, 023202	1.3	1
4	Al Composition Dependence of Band Offsets for SiO2 on <code>E(AlxGa1M)2O3</code> . <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 113007	2	1
3	Effects of Downstream Plasma Exposure on EGa2O3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> ,	2	1
2	Annealing of Proton and Alpha Particle Damage in Au-W/EGa2O3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P799-P804	2	1

Annealing Effects on the Band Alignment of ALD SiO2 on $(InxGa1 \ 2003)$ for $x = 0.25 \ 2000$. Annealing Effects on the Band Alignment of ALD SiO2 on $(InxGa1 \ 2003)$ for $x = 0.25 \ 2000$. Annealing Effects on the Band Alignment of ALD SiO2 on $(InxGa1 \ 2003)$ for $x = 0.25 \ 2000$.

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